

Notice of Allowability	Application No.	Applicant(s)	
	10/540,720	KISHIMA ET AL.	
	Examiner David Nhu	Art Unit 2818	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. This communication is responsive to 12/14/07.
2. The allowed claim(s) is/are 1,4-7 and 11-17.
3. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) All
 - b) Some*
 - c) None
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

* Certified copies not received: _____.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.
THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

4. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
5. CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
 - (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 - 1) hereto or 2) to Paper No./Mail Date _____.
 - (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date _____.

Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).
6. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

- | | |
|---|---|
| <ol style="list-style-type: none"> 1. <input type="checkbox"/> Notice of References Cited (PTO-892) 2. <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) 3. <input type="checkbox"/> Information Disclosure Statements (PTO/SB/08),
Paper No./Mail Date _____ 4. <input type="checkbox"/> Examiner's Comment Regarding Requirement for Deposit
of Biological Material | <ol style="list-style-type: none"> 5. <input type="checkbox"/> Notice of Informal Patent Application 6. <input type="checkbox"/> Interview Summary (PTO-413),
Paper No./Mail Date _____ 7. <input type="checkbox"/> Examiner's Amendment/Comment 8. <input checked="" type="checkbox"/> Examiner's Statement of Reasons for Allowance 9. <input type="checkbox"/> Other _____. |
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EASONS FOR ALLOWANCE

1. Claims 1, 4-7, 11-17 are allowed.
2. The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests as cited in claims 1, 11: forming a silicon dioxide layer in the single crystal silicon substrate by heat treatment; and removing the mask and the surface protection layer from the single silicon substrate, wherein the silicon dioxide layer has a pattern corresponding to presence/absence and thickness of the mask formed on the major surface of the single-crystal silicon substrate, the pattern having a relatively short distance from the major surface in an area where the mask has been formed and a relatively long distance from the major surface in an area where the mask has not been formed (as cited in claim 1); forming a silicon dioxide layer in the single-crystal silicon substrate by heat treatment; removing the mask and the surface protection layer; and polishing the major surface by a predetermined quality; wherein the silicon dioxide layer has a pattern such that its distance from the major surface in an area where the mask has been formed on the major surface is relatively short while its distance from the major surface in an area where the mask has not been formed is relatively long, and the quantity of polishing is equal to the quantity of removal of the silicon dioxide layer formed in area where the mask has been formed (as cited in claim 11).
3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

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4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Yamazaki et al (6,803,264 B2): Method of Fabricating a Semiconductor Device.
5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to David Nhu, (703) 306-5796.

The examiner can normally be reached on Monday-Friday from 7:30 AM to 5:00 PM.

The fax phone number for the organization where this application or proceeding is assigned is (571)273-8300.

David Nhu



December 28, 2007



DAVID NHU
PRIMARY EXAMINER